L Number	Hits	Search Text	DB	Time stamp
1	13657	((438/149) or (438/174) or (438/176) or	USPAT;	2004/07/31 20:26
į		(438/180) or (438/181) or (438/184) or	US-PGPUB;	
		(438/185) or (438/197) or (438/199) or	EPO; JPO;	
,		(438/201) or (438/207) or (438/211) or	DERWENT;	
		(438/213) or (438/217) or (438/218) or	IBM_TDB	
		(438/221) or (438/222) or (438/229) or		
		(438/230) or (438/231) or (438/233) or		
		(438/260) or (438/265) or (438/276) or		
		(438/289) or (438/294) or (438/296) or		
		(438/299) or (438/300) or (438/301) or		
		(438/303) or (438/311) or (438/318) or		
		(438/320) or (438/364) or (438/406) or (438/413) or (438/416) or (438/429) or		
		(438/430) or (438/459) or (438/488) or		
		(438/491) or (438/532) or (438/597) or		
		(438/607) or (438/704)).CCLS.		
2	31127	l	USPAT;	2004/07/31 20:28
_			US-PGPUB;	,,
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
3	109204	cmos or (complementary near (metal near2	USPAT;	2004/07/31 20:31
ŀ		oxide))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		•	IBM_TDB	
4	2814	simox or (separation adj ion adj	USPAT;	2004/07/31 20:32
		implantation adj oxygen)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_		(6) 13 13 15 11	IBM_TDB	0004/05/04 00 00
5	1333	(front and back) near5 gate	USPAT;	2004/07/31 20:33
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
6	154699	gate near5 (dielectric or insulat\$3 or	USPAT;	2004/07/31 20:34
9	134099	oxide)	US-PGPUB;	2004/07/31 20:34
		ONTAC	EPO; JPO;	
			DERWENT;	
			IBM TDB	1
7	85681	trench\$2	USPAT;	2004/07/31 20:34
ŀ			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
İ			IBM_TDB	
8	4	sacrifical near3 spacer\$1	USPAT;	2004/07/31 21:21
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
9	10	sacrifical same spacer\$1	IBM_TDB USPAT;	2004/07/21 20:35
,	10	sacrifical same spacersi	US-PGPUB;	2004/07/31 20:35
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
10	7641	(soi or (silicon near2 insulator)) and (cmos	USPAT;	2004/07/31 20:36
· -		or (complementary near (metal near2 oxide)))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
11	1178	((soi or (silicon near2 insulator)) and	USPAT;	2004/07/31 20:43
l		(cmos or (complementary near (metal near2	US-PGPUB;	
		oxide)))) and (simox or (separation adj ion	EPO; JPO;	
		adj implantation adj oxygen))	DERWENT;	
		[, , , , , , , , , , , , , , , , , , ,	IBM_TDB	1
12	32	(((soi or (silicon near2 insulator)) and	USPAT;	2004/07/31 20:43
		(cmos or (complementary near (metal near2	US-PGPUB;	1
		oxide)))) and (simox or (separation adj ion	EPO; JPO;	
		adj implantation adj oxygen))) and ((front	DERWENT;	
		and back) near5 gate)	IBM_TDB	

13	32	((((soi or (silicon near2 insulator)) and	USPAT; US-PGPUB;	2004/07/31 20:44
		(cmos or (complementary near (metal near2 oxide)))) and (simox or (separation adj ion	EPO; JPO;	·
		adj implantation adj oxygen))) and ((front	DERWENT;	
		and back) near5 gate))	IBM_TDB	
16	0	((((((soi or (silicon near2 insulator)) and	USPAT;	2004/07/31 20:45
		(cmos or (complementary near (metal near2 oxide)))) and (simox or (separation adj ion	US-PGPUB; EPO; JPO;	
		adj implantation adj oxygen))) and ((front	DERWENT;	
İ		and back) near5 gate)) and (gate near5	IBM_TDB	
		(dielectric or insulat\$3 or oxide))) and		
15	16	trench\$2) and (sacrifical same spacer\$1) (((((soi or (silicon near2 insulator)) and	USPAT;	2004/07/31 20:53
13		(cmos or (complementary near (metal near2	US-PGPUB;	2001/07/31 20:33
		oxide)))) and (simox or (separation adj ion	EPO; JPO;	
		adj implantation adj oxygen))) and ((front	DERWENT;	
		and back) near5 gate)) and (gate near5 (dielectric or insulat\$3 or oxide))) and	IBM_TDB	
		trench\$2		
17	1	l	USPAT;	2004/07/31 20:47
		(cmos or (complementary near (metal near2	US-PGPUB;	
		oxide)))) and (simox or (separation adj ion adj implantation adj oxygen))) and ((front	EPO; JPO; DERWENT;	
		and back) near5 gate)) and (gate near5	IBM TDB	
		(dielectric or insulat\$3 or oxide))) and		
		trench\$2) and (((438/149) or (438/174) or		
	1	(438/176) or (438/180) or (438/181) or		
	1	(438/184) or (438/185) or (438/197) or (438/199) or (438/201) or (438/207) or		
		(438/211) or (438/213) or (438/217) or		
		(438/218) or (438/221) or (438/222) or		
		(438/229) or (438/230) or (438/231) or		
		(438/233) or (438/260) or (438/265) or		
		(438/276) or (438/289) or (438/294) or (438/296) or (438/299) or (438/300) or		
		(438/301) or (438/303) or (438/311) or		
		(438/318) or (438/320) or (438/364) or		
		(438/406) or (438/413) or (438/416) or		
		(438/429) or (438/430) or (438/459) or (438/488) or (438/491) or (438/532) or		
		(438/597) or (438/607) or (438/704)).CCLS.)		
18	9	("6074209" "6275094" "6359312"	USPAT	2004/07/31 21:11
		"6383904" "6391695" "6392277"		
37	16	"6423599" "6432754" "6441436").PN. ("3853633" "4222062" "4393578"	USPAT	2004/07/31 21:14
37	**	"4839707" "4951123" "5166765"	OSPAI	2004/07/31 21:14
		"5273921" "5285352" "5376578"		
		"5482871" "5726459" "5780912"		
		"6008126" "6057555" "6074920" "6166412").PN.		
38	9	("6074209" "6275094" "6359312"	USPAT	2004/07/31 21:17
		"6383904" "6391695" "6392277"		,,
	_ :	"6423599" "6432754" "6441436").PN.		
45	7	,	USPAT	2004/07/31 21:19
		"6284594" "6359298" "6365450" "6376312").PN.		
46	350479	spacer\$1	USPAT;	2004/07/31 21:21
		- ·	US-PGPUB;	, ,
			EPO; JPO;	
			DERWENT; IBM TDB	
47	9	("4601779" "5273921" "5296727"	USPAT	2004/07/31 21:23
		"5461250" "5497019" "5604368"		,,
1.4		"5681775" "5929479" "6248637").PN.		
14	32	<pre>((((soi or (silicon near2 insulator)) and (cmos or (complementary near (metal near2</pre>	USPAT;	2004/07/31 21:28
	[oxide)))) and (simox or (separation adj ion	US-PGPUB; EPO; JPO;	
		adj implantation adj oxygen))) and ((front	DERWENT;	
		and back) near5 gate)) and (gate near5	IBM_TDB	
62		(dielectric or insulat\$3 or oxide))	I I I I I I I I I I I I I I I I I I I	0004/07/04 55 55
62	4	("5291047" "5446299" "5488243" "5751037").PN.	USPAT	2004/07/31 21:31
	L	3/3±03/ /.EM.	l	L

63 19 | 5929479.URPN. USPAT 2004/07/31 21:32